

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N2218
2N2218A
2N2219
2N2219A

NPN Silicon Transistor
JEDEC TO-39 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N2218,A,2N2219,A are Silicon NPN Planar Epitaxial Transistors designed for small signal general purpose and switching applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

		2N2218 2N2219	2N2218A 2N2219A	
Collector-Base Voltage	V_{CB0}	60	75	Vdc
Emitter-Base Voltage	V_{EB0}	5.0	6.0	Vdc
Collector-Emitter Voltage	V_{CE0}	30	40	Vdc
Collector Current-Continuous	I_C		800	mAdc
Power Dissipation	P_T		0.8	watts
Power Dissipation, $T_C=25^\circ\text{C}$	P_T		3.0	watts
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200 $^\circ\text{C}$		

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Symbol	Test Conditions	2N2218 2N2219		2N2218A 2N2219A		Unit
		Min	Max	Min	Max	
I_{CBO}	$V_{CB}=50\text{V}$		10			nA
I_{CBO}	$V_{CB}=60\text{V}$			10		nA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$			10		nA
I_{EBO}	$V_{EB}=3.0\text{V}$		10	10		nA
BV_{CBO}	$I_C=10\mu\text{A}$	60		75		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		6.0		V
BV_{CEO}	$I_C=10\text{mA}$	30		40		V
$V_{CE}(s)$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4		0.3	V
$V_{CE}(s)$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.6		1.0	V
$V_{BE}(s)$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3		1.2	V
$V_{BE}(s)$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.6		2.0	V
		2N2218 2N2218A		2N2219 2N2219A		Unit
		Min	Max	Min	Max	
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$	20		35		-
h_{FE}	$V_{CE}=10\text{V}, I_C=1\text{mA}$	25		50		-
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	35		75		-
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	40	120	100	300	-
h_{FE}	$V_{CE}=1\text{V}, I_C=150\text{mA}$	20		50		-
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$ (2N2218, 2N2219 Only)	20		30		-
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$ (2N2218A, 2N2219A Only)	25		40		-
f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$ (Except 2N2219A)	250		250		MHz
f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$ (2N2219A Only)			300		MHz
C_{ob}	$V_{CB}=10\text{V}, f=100\text{kHz}$		8.0		8.0	pF
t_{ON}	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_B=15\text{mA}$		35		35	ns
t_{OFF}	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		285		285	ns